



## 单向硅整流桥堆

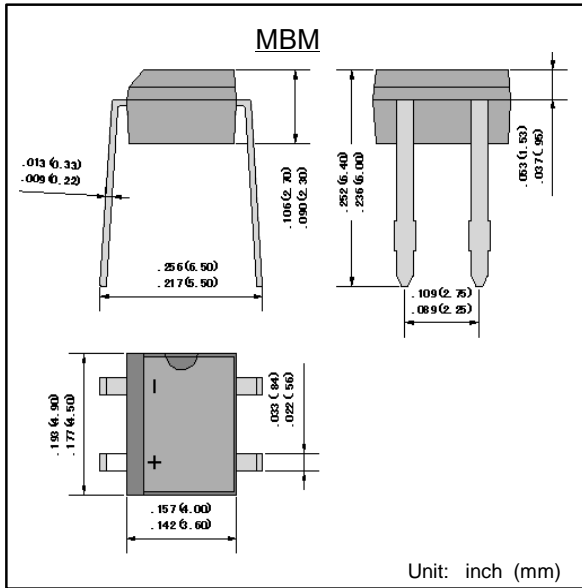
反向电压 200 ~ 1000 V

正向电流 0.5 A

## Single phase Silicon Bridge Rectifiers

Reverse Voltage 200 ~ 1000 V

Forward Current 0.5 A



### 特征 Features

- 反向漏电流低 Low reverse leakage
- 正向浪涌承受能力强 High forward surge capability
- 高温焊接保证 High temperature soldering guaranteed:
- 玻璃钝化芯片 Glass passivated chip  
260°C/10 秒 260°C/10seconds
- 引线 and 管体皆符合RoHS标准。  
Lead and body according with RoHS standard

### 机械数据 Mechanical Data

- 封装: MBM 塑料封装 Case: MBM Molded plastic
- 极性: 标记模压或印于本体  
Polarity: Symbols molded or marked on body
- 安装位置: 任意 Mounting Position: Any

### 最大值和特性 TA = 25°C 除非另有规定。

### Maximum Ratings & Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

参数 Parameter	符号 Symbols	MB2M	MB4M	MB6M	MB8M	MB10M	单位 Unit
最大可重复峰值反向电压 Maximum repetitive peak reverse voltage	$V_{RRM}$	200	400	600	800	1000	V
最大均方根电压 Maximum RMS voltage	$V_{RMS}$	140	280	420	560	700	V
最大直流阻断电压 Maximum DC blocking voltage	$V_{DC}$	200	400	600	800	1000	V
最大正向平均整流电流 Maximum average forward rectified current	$I_{F(AV)}$	0.5					A
正向不重复浪涌电流 8.3 ms单一正弦半波 Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	$I_{FSM}$	35					A
最大正向电压 @IF=0.4A Maximum forward voltage	$V_F$	1.0					V
最大反向电流 @V <sub>DC</sub> Maximum reverse current	$I_R$	5					μA
典型热阻 Typical thermal resistance (Note 1)	R <sub>θJA</sub>	85					°C/W
	R <sub>θJL</sub>	20					
工作结温和存储温度 Operating junction and storage temperature rang	T <sub>J</sub> , T <sub>STG</sub>	-55 --- +150					°C

备注 Note:

1) 安装在PCB板上, 从PN结到环境的热阻。

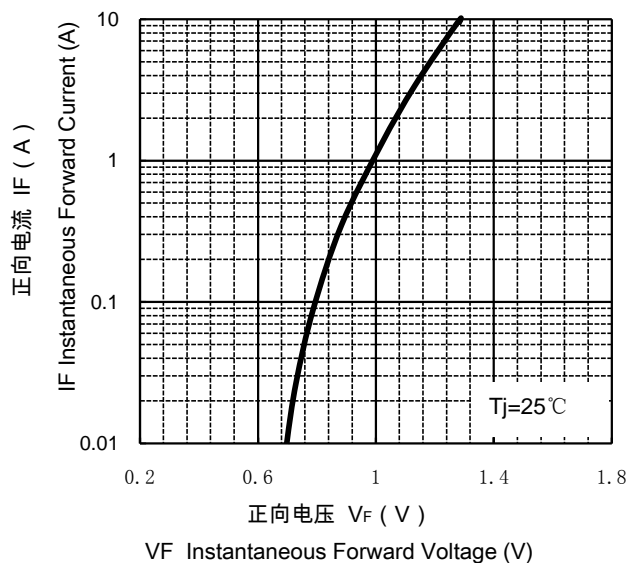
1) Thermal resistance from junction to ambient, PCB mounted.



## 特性曲线 Characteristic Curves

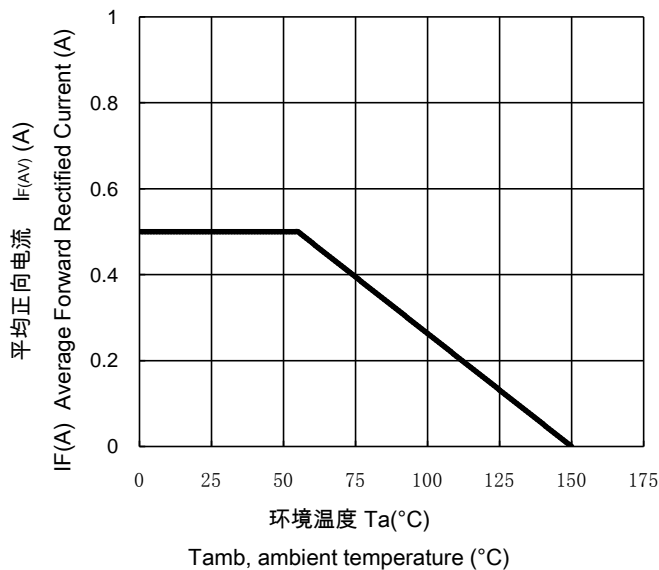
正向特性曲线 (典型值)

TYPICAL FORWARD CHARACTERISTIC



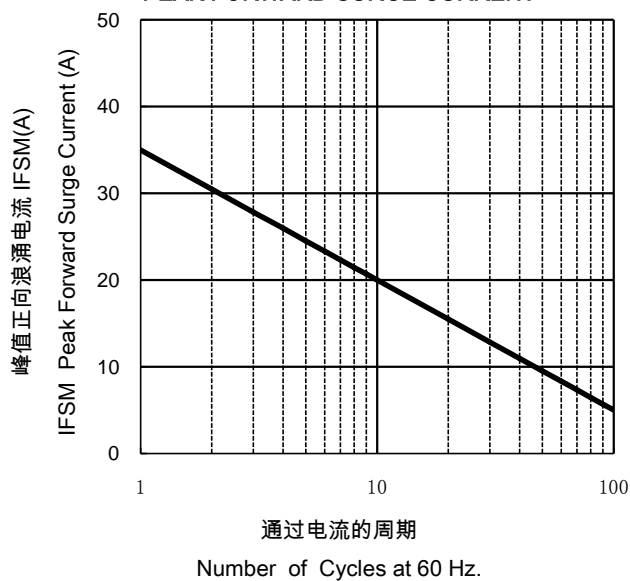
正向电流降额曲线

FORWARD CURRENT DERATING CURVE



浪涌特性曲线 (最大值)

MAXIMUM NON REPETITIVE PEAK FORWARD SURGE CURRENT



反向特性曲线

Typical Reverse Characteristics

